TOSHIBA

#### TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

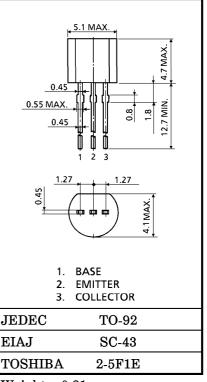
# 2 S C 2 4 9 8

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATION

Unit in mm

#### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{\mathrm{CBO}}$	30	V
Collector-Emitter Voltage	$v_{CEO}$	20	V
Emitter-Base Voltage	$v_{\mathrm{EBO}}$	3	V
Collector Current	$I_{\mathbf{C}}$	50	mA
Base Current	$I_{\mathbf{B}}$	25	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	300	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C



Weight: 0.21 g

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## MICROWAVE CHARACTERISTICS (Ta = 25°C)

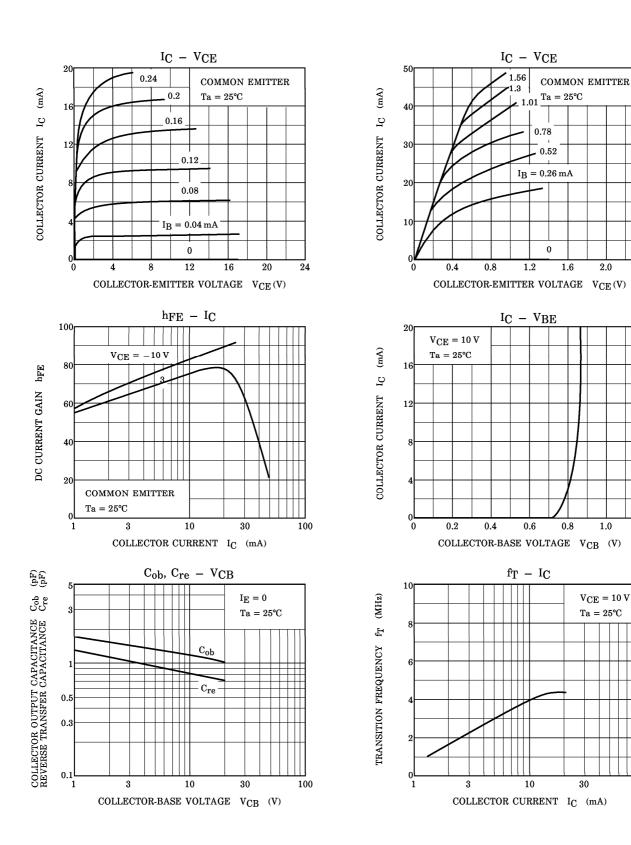
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$ m f_{T}$	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$	_	3.5		GHz
Insertion Gain	$ S_{2le} ^2(1)$	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}, $ f = 500 MHz	_	14.5	_	- dB
	$ S_{2le} ^2(2)$	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA},$ f = 1  GHz	_	9	_	
Noise Figure	NF (1)	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}, $ f = 500 MHz	_	2.5	_	dB
	NF (2)	$V_{ ext{CE}} = 10 \text{ V}, I_{ ext{C}} = 5 \text{ mA},$ $f = 1 \text{ GHz}$	_	4	_	αБ

## MICROWAVE CHARACTERISTICS (Ta = 25°C)

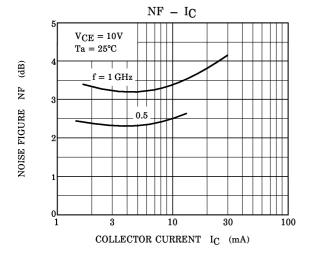
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	1	$\mu$ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = 1 V, I_{C} = 0$	_	_	1	$\mu$ A
DC Current Gain	$h_{ extbf{FE}}$	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$	30	80	300	_
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	1.15	_	
Reverse Transfer	$\mathrm{C_{re}}$	(Note)		0.75		рF
Capacitance	Ore	(11000)	_	0.75	_	

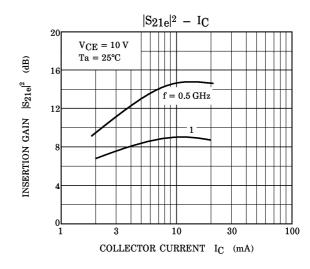
(Note): Cre is measured by 3 terminal method with Capacitance Bridge.

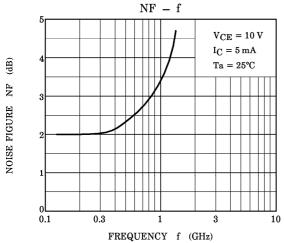
2.4

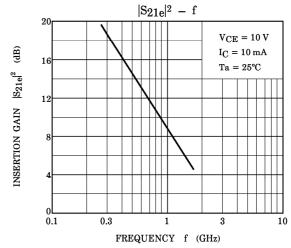


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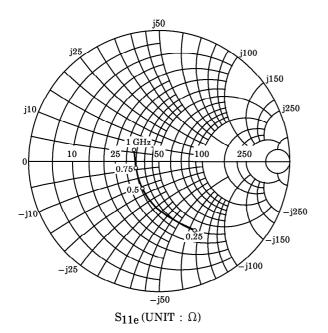


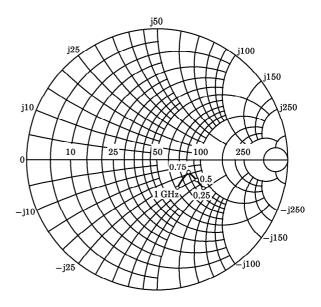




### COMMON EMITTER SMALL SIGNAL S-PARAMETERS OF 2SC2498.

 $V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$ 





 $S_{22e}\left(UNIT:\Omega\right)$ 

